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BRS	SAS	BRS	BRS	BRS	BRS	BRS	BRS	Туре
L19	гċ	E ©	L7	16	E G	14	r.	۲ #
(n -1 -1	p4	115	63	υ		281	2887	Hits
(stress with (buffer adj layer))	L8 and porous	14 and (semiconductor or chip or die or wafer)	14 and (semiocnductor or chip cr die or wafer)	l3 and (stress near layer)	13 and 14	stress adj relax\$ adj layer	circuit adj layer	Search Text
HSPAT; HS-PGPU B; EPO; JFO; FFRWENT ; IEM	USPAT; US-PGPU B; EPO; JFO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	, , , c	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	H C	H •• C	DBs
2001/38/11	2001/08/21	2001/08/21	2001/08/21	2001/08/21	2001/08/21 12:54	2001/08/21 15:26	2001/08/21	Time Stamp
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16 BRS	15 BRS	14 BRS	13 BRS	12 BRS	11 BRS	10 BRS	
11.6	L17	L16	L15	L14	L13	L12	t i
co d	¢0	98	269	4	ω	267	F
L15 with (Lemis or chip or wafer)	L15 near (zemi\$ or chip or wafer)	L15 and (semi\$ or chip)	organic near (protect\$ adj film)	(chip with ((buffer adj layer) or (stress with layer))) and (circuit adj layer)	L3 and L12	porous adj tape	L10 and 13
USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	□	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM ; IDB	H C	н
2001/08/11 14:42	2001/08/21	2001/ṇṣ/21 14:06	2001/08/21 14:03	2001/08/21	2001/08/21 13:33	2001/08/21 13:33	13:32
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87. C	BRS	BRS	BRS	BRS	BRS	BRS	BRS	Туре
6	125	L24	L23	L22	L21	L20	L19	#
54767	372	61972	210113	34	39	369	369	Hits
porous with layer	L24 and (circuit adj layer)	L23 and (semiconductor or chip or wafer)	(porous or gap or space or hole) with layer	(porous or gap or space or hole) with ( stress adj ((relax\$ or buffer) adj layer))	L20 and ((porous or hole\$ or space\$ or gap) with layer)	((prevent or stop or less) near warp\$) with (chip or die or semiconductor or wafer)	((prevent or stp or less) near warp\$) with (chip or die or semiconductor or wafer)	Search Text
USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	₽ ∵⊂	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	H C	DBs
2001/38/21 16:39	2001/08/21 16:40	2001/08/21	2001/08/21 16:39	2001/08/21 16:31	2001/08/21 15:20	2001/08/21 15:18	2001/08/21	Time Stamp
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w ci	(u)	30	29	28	27	26	25	
BRS	BRS	BRS	BRS	BRS	BRS	BRS	BRS	Туре
L34	L31	L33	L32	L30	L29	L28	L27	# 1
1.2	551	<u></u>	C	1381	3	29	4768	Hits
L31 and (procests with (film or liner or layer))	257/569.ccls.	L31 and trace and (stress with layer)	L31 and (circuit adj layer)	L3 and (semiconductor or chip or wafer or die)	(porous near (tape or polymide)) and (circuit adj layer)	L27 and (circuit adj layer)	L26 and (semiconductor or chip or wafer)	Search Text
USPAT; US-PGPU B; EPO; JFO; DERWENT ; 1BM	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	USPAT; US-PGPU E; EPO; JPO; DERWENT ; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM TDB	. ⊣ ∵ ⊂	DBs
18:07	2001/08/21 18:11	2001/08/21	2001/08/21 17:59	2001/08/21 17:56	2001/08/21 17:00	2001/08/21 16:58	2001/08/21 16:40	Time Stamp
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257/635.ccls. and stress	157/635.ccls. and wafer	257/668.ccls. and wafer	(wafer adj (compris\$ or consist\$)) with ((via or through) adj hole)	(wafer adj (compris\$ or consist\$)) with (via adj hole)	257/913.ccls. and stress	257/913.ccls. and wafer	257/668.ccls. and wafer
USPAT; US-PGPU B; EPO; JPO; DERWEN: ; IBM	USPAT; US-PGFU B; EPO; JPO; JPO; DERWENT ; IEM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	H C	7	1 " -	H C
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16 BRS	m m m	14 BRS	13 BRS	12 BRS	11 BRS	10 BRS	9 BRS	Type
L16	L15	Г14	Т13	Г12	L11	L10	Г9	- - - -
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(porous adj polytetrafluorce:hylene) same stress	porcus adj polytetraflucroethylene JPO; portus adj polytetraflucroethylene JPO; 1 IB	porous near polytetrafluorcethylene	porous with polytetrafluorcethylene	L10 and package	L10 and wafer	stress adj relax\$ adj layer	257/638.ccls. and stress	Search text
USPAT; US-PGPU B; EPO; JPO; DERWENT	USPAT; US-PGPU B; EPO; ene JPO; DERWENT; IBM TDB	US-PGPU B; EPG; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IEM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT ; IBM ; TDB	USPAT; US-PGPU B; EPO; JPO; DERWENT; IBM TDB	
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T					USPAT;		,		
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	_	******			; IBM				
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2	ti Z	- C C		hole)	DERWENT	60.00		5.0.0.CON	
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